L Number	Hits	Search Text	DB	Time stamp
1	30635	thermal$5 near5 treat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:03
2	1120801	alignment aligning orientation orienting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:03
3	33719	source adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:03
4	33687	drain adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:03
5	2	(thermal$5 near5 treat$3) same (alignment aligning orientation orienting) same (source adj electrode) same (drain adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:04
6	121	simultaneously near5 (thermal$5 near5 treat$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:04
7	1	(simultaneously near5 (thermal$5 near5 treat$3)) same (alignment aligning orientation orienting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:05
8	0	(simultaneously near5 (thermal$5 near5 treat$3)) and 349$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:05
9	11	(simultaneously near5 (thermal$5 near5 treat$3)) and 257$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 09:05

L Number	Hits	Search Text	DB	Time stamp
1	551	349/141.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:43
2	661	349/187.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:43
3	2063	(257/59,72).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:43
4	82970	(gate scan$4) adj (line wir$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:44
5	1348093	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:44
6	1399664	insulat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:44
7	48220	(pixel display picture) near2 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:44
8	1338785	channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:44
9	1141459	alignment aligning orientation orienting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:45
10	6789	thermal-treat$3 (thermal adj treat$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:45
11	53031	(source drain) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:45
12	4	(thermal-treat$3 (thermal adj treat$3)) same ((source drain) adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:46

13	35	((gate scan$4) adj (line wir$3)) same semiconductor same insulat$3 same ((pixel display picture) near2 electrode) same channel same (alignment aligning orientation orienting) same ((source drain) adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:47
14	4	349/141.ccls. and (((gate scan$4) adj (line wir$3)) same semiconductor same insulat$3 same ((pixel display picture) near2 electrode) same channel same (alignment aligning orientation orienting) same ((source drain) adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:47
15	2	349/187.ccls. and (((gate scan$4) adj (line wir$3)) same semiconductor same insulat$3 same ((pixel display picture) near2 electrode) same channel same (alignment aligning orientation orienting) same ((source drain) adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:48
16	3534	((gate scan$4) adj (line wir$3)) same semiconductor same insulat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:48
17	6897	((pixel display picture) near2 electrode) same (alignment aligning orientation orienting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:48
18	1505	(((gate scan$4) adj (line wir$3)) same semiconductor same insulat$3) same ((source drain) adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:49
19	538	(((pixel display picture) near2 electrode) same (alignment aligning orientation orienting)) and ((((gate scan$4) adj (line wir$3)) same semiconductor same insulat$3) same ((source drain) adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:49
20	46	349/141.ccls. and ((((pixel display picture) near2 electrode) same (alignment aligning orientation orienting)) and ((((gate scan$4) adj (line wir$3)) same semiconductor same insulat$3) same ((source drain) adj electrode)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:49
21	24	349/187.ccls. and ((((pixel display picture) near2 electrode) same (alignment aligning orientation orienting)) and ((((gate scan$4) adj (line wir$3)) same semiconductor same insulat$3) same ((source drain) adj electrode)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:49
22	414762	mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:49
23	63372	pattern$3 near5 metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:50
24	7500	(pattern$3 near5 metal) near10 mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:50

25	71756	(common counter) adj (electrode line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:50
26	7	((pattern$3 near5 metal) near10 mask) same ((common counter) adj (electrode line)) same ((gate scan$4) adj (line wir$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:50
27	6004	(pattern$3 near5 metal) near10 semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:51
28	2	(((pattern$3 near5 metal) near10 mask) same ((common counter) adj (electrode line)) same ((gate scan$4) adj (line wir$3))) and ((pattern$3 near5 metal) near10 semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:53
29	39	lee-yun-bok.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:53
31	0	349/187.ccls. and lee-yun-bok.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:53
30	10	349/141.ccls. and lee-yun-bok.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 07:53